# MSKSEMI 美森科













ESD

TVS

TSS

MOV

GDT

PLED

ESD05V14T-MS

# Product specification



# ESD05V14T-MS

#### Features

- 350 W Peak Power per Line (tp = 8/20µs)
- SOT-143 package
- ESD Protection > 15 kV
- Unidirectional configurations
- Protects 2 I/O Ports & Power Supply
- Low clamping voltage
- RoHS Compliant in Lead-Free Versions
- Transient protection for data lines to IEC 61000-4-2(ESD) ±15KV(air) ±8KV(contact); IEC 61000-4-4 (EFT) 40A (5/50ns)

#### **Mechanical Characteristics**

- Lead finish:100% matte Sn(Tin)
- Mounting position: Any
- Qualified max reflow temperature: 260 C
- Device meets MSL 1 requirements
- Pure tin plating: 7 ~ 17 um
- Pin flatness:≤3mil

#### **Reference News**

PACKAGE OUTLINE	Pin Configuration	Marking
		WR1*

#### Applicati

- Ethernet 10/100 Base T
- Fire wire
- Wireless communications
- USB interface



#### Electrical Characteristics(TA=25°C unless otherwise specified)

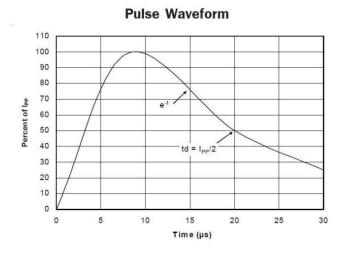
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Units
Reverse Stand-off Voltage	Vrwm				5	V
Reverse Breakdown Voltage	Vbr	It = 1mA	6		8.5	V
Reverse Leakage Current	lr	V <sub>RWM</sub> =5.0V, T=25C			1	μA
Clamping Voltage	Vc	I <sub>PP</sub> = 1A, t <sub>P</sub> = 8/20µs			12.5	V
Clamping Voltage	Vc	I <sub>PP</sub> =5A, t <sub>P</sub> = 8/20µs			24.0	V
Capacitance Between IO and GND	Cı	V <sub>R</sub> =0V, f = 1MHz		3.0		pF
Capacitance Between IO and I/O	Сл	V <sub>R</sub> =0V, f = 1MHz		1.5		pF

## Absolute maximum rating@25°C

Rating	Symbol	Value	Units
Peak Pulse Power (t <sub>p</sub> =8/20µs)	Ppp	350	W
Peak Pulse Power (t <sub>p</sub> =8/20µs)	Ipp	9	А
Operating Temperature	TJ	-55 to + 150	°C
Storage Temperature	Тѕтс	-55 to + 150	°C

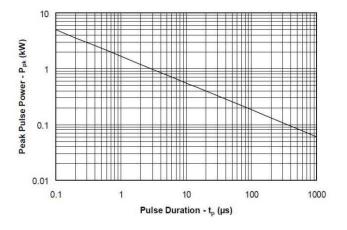


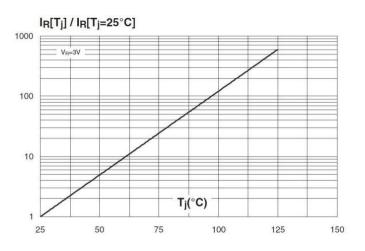
#### Typical Characteristics@ Ta=25℃ unless otherwise specified



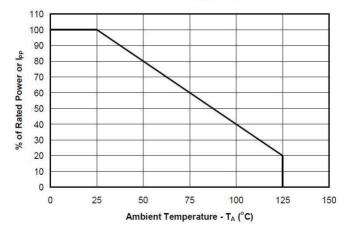
ICONDUCTOR

#### Non-Repetitive Peak Pulse Power vs. Pulse Time



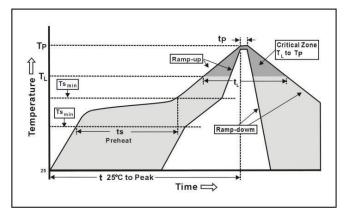


**Power Derating Curve** 



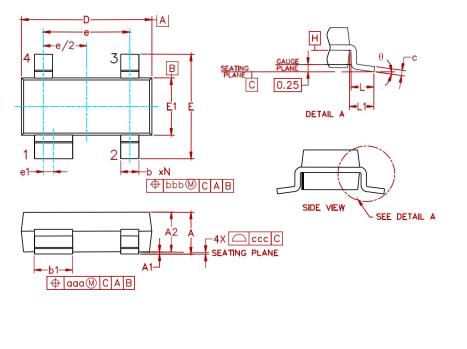
## SolderingParameters

Reflow Condition		Fb – Free assembly	
	- Temperature Min (T <sub>s(Min)</sub> )	150°C	
Pre Heat	- Temperature Max (T <sub>s(Max)</sub> )	200°C	
	-Time (Min to max) (t <sub>s</sub> )	60 – 180 secs	
Average ramp up rate (Liquidus) Temp (T <sub>L</sub> ) to peak		3°C/second Max	
T <sub>s (Max)</sub> to T <sub>L</sub> - Ramp-up Rate		3°C/second Max	
Reflow	-Temperature (T <sub>L</sub> ) (Liquidus)	217°C	
	-Temperature (t <sub>L</sub> )	60 – 150 seconds	
Peak Temperature (T <sub>p</sub> )		250 <sup>+0/-5</sup> °C	
Time within 5°C of actual peak Temperature (t <sub>p</sub> )		20 – 40 seconds	
Ramp-dowm Rate		6°C/second Max	
Time 25°C to peak Temperature (T <sub>P</sub> )		8 minutes Max.	
Do not exceed		260°C	



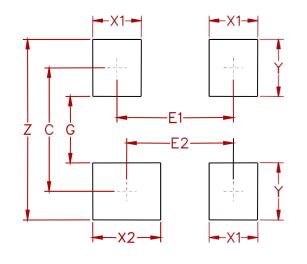


## PACKAGE MECHANICAL DATA



Symbol	Inches			Millimeters		
Symbol	Min.	Nom.	Max.	Min.	Nom.	Max.
Α	0.031	-	0.048	0.80	-	1.22
A1	0.000	-	0.008	0.013	-	0. 15
A2	0.020	0.035	0.042	0.75	0.90	1.07
b	0.011	-	0.020	0.30	-	0.51
b1	0.029	-	0.037	0.76	-	0.94
с	0.003	-	0.008	0.08	-	0.20
D	0. 110	0. 114	0. 120	2.80	2.90	3.04
E	0.082	0.093	0. 104	2. 10	2.37	2.64
E1	0.047	0.051	0.055	1.20	1.30	1.40
е	0.075			1.92 BSC		
e1	0.008			0.20 BSC		
L	0.015	0.020	0.024	0.40	0.50	0.60
L1	(0.021)			(0.54)		
N	4			4		
θ	0.	-	8.	0.	-	8.
aaa	0.006			0. 15		
bbb	0.008			0.20		
ссс	0.004			0. 10		

## **Suggested Pad Layout**



#### Note:

1.Controlling dimension: in millimeters.

2.General tolerance:±0.05mm.

3. The pad layout is for reference purposes only.

#### **REEL SPECIFICATION**

P/N	PKG	QTY
ESD05V14T-MS	SOT-143	3000



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